Product data sheet

1. General description

PNP low V_{CEsat} transistor in a SOT457 (SC-74) small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS303ND

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- · High efficiency due to less heat generation
- · Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

3. Applications

- High-voltage DC-to-DC conversion
- High-voltage MOSFET gate driving
- · High-voltage motor control
- · High-voltage power switches (e.g. motors, fans)
- · Thin Film Transistor (TFT) backlight inverter
- Automotive applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	-60	V
I _C	collector current		[1]	-	-	-3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-6	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -2 A; I_B = -200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	75	100	mΩ

[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	С	collector		6
2	С	collector	<u> </u>	C
3	В	base		В
4	Е	emitter) E
5	С	collector	TSOP6 (SOT457)	sym030
6	С	collector		

6. Ordering information

Table 3. Ordering information

Type number	Package	ckage				
	Name	Description	Version			
PBSS303PD	TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS303PD	АН

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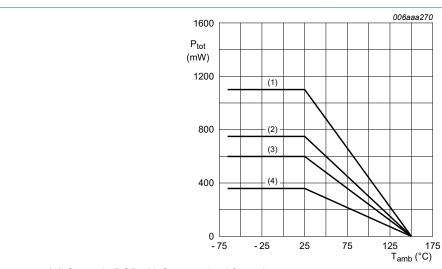
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-60	V
V _{CEO}	collector-emitter voltage	open base		-	-60	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current		[1]	-	-1	Α
			[2]	-	-3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-6	Α
I _B	base current			-	-800	mA
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	-2	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	360	mW
			[3]	-	600	mW
			[4]	-	750	mW
			[2]	-	1.1	W
			[1] [5]	-	2.5	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [5] Pulse test: $t_p \le 10 \text{ ms}$; $\delta \le 10 \%$.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, mounting pad for collector 1 cm²
- (4) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance fro junction to ambient	thermal resistance from	in free air	[1]	-	-	350	K/W
		[2]	-	-	208	K/W	
		[3] [4] [1] [5]	[3]	-	-	167	K/W
			-	-	113	K/W	
			[1] [5]	-	-	50	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	45	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Pulse test: $t_p \le 10$ ms; $\delta \le 10$ %.

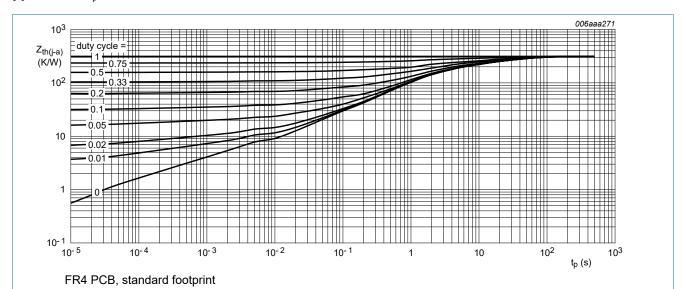


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

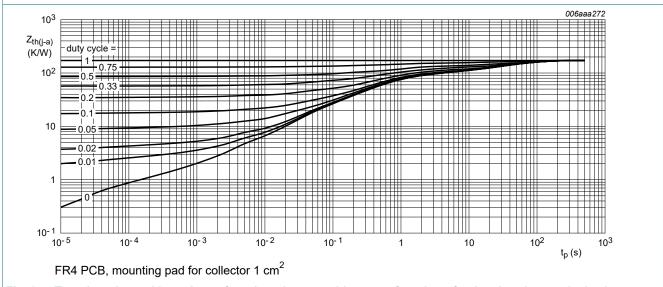


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

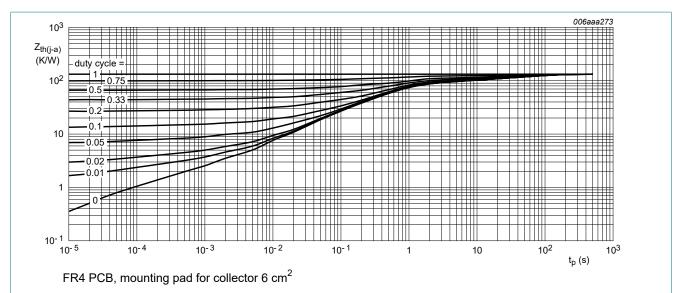


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

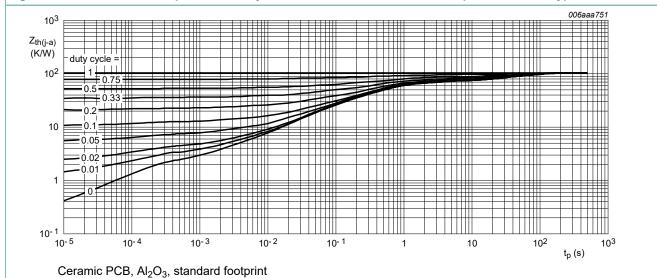


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Сво	collector-base cut-off	V _{CB} = -60 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -60 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μΑ
EBO	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
CES	collector-emitter cut-off current	V _{CE} = -48 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
) _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -500 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	180	265	-	
		V_{CE} = -2 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	160	235	-	
		V_{CE} = -2 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	130	185	-	
		V_{CE} = -2 V; I_{C} = -3 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	95	135	-	
		V_{CE} = -2 V; I_{C} = -4 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	60	80	-	
		V_{CE} = -2 V; I_{C} = -5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	35	50	-	
		V_{CE} = -2 V; I_{C} = -6 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	20	30	-	
V _{CEsat}	collector-emitter	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	-55	-70	mV
	saturation voltage	$I_C = -1 \text{ A}; I_B = -50 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	-100	-135	mV
		I_C = -2 A; I_B = -200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-150	-200	mV
		I_C = -3 A; I_B = -150 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-275	-365	mV
		I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-210	-290	mV
		I_C = -4 A; I_B = -400 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-285	-385	mV
		I_C = -5 A; I_B = -500 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-375	-495	mV
		I_C = -6 A; I_B = -600 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-515	-675	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = -2 A; I_B = -200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	75	100	mΩ
/ _{BEsat}	base-emitter saturation	I_C = -500 mA; I_B = -50 mA; T_{amb} = 25 °C	-	-0.78	-0.87	V
	voltage	I _C = -1 A; I _B = -50 mA; T _{amb} = 25 °C	-	-0.8	-0.89	V
		I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.83	-0.92	V
		I_C = -3 A; I_B = -150 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.92	-0.99	V
		I_C = -3 A; I_B = -300 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.94	-1.02	V
/ _{BEon}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; I_{C} = -2 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-0.8	-1	V

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _d	delay time	$V_{CC} = -9.2 \text{ V}; I_C = -2 \text{ A}; I_{Bon} = -0.1 \text{ A};$	-	13	-	ns
t _r	rise time	I _{Boff} = 0.1 A; T _{amb} = 25 °C	-	53	-	ns
t _{on}	turn-on time		-	66	-	ns
t _s	storage time		-	230	-	ns
t _f	fall time		-	76	-	ns
t _{off}	turn-off time		-	306	-	ns
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C	-	110	-	MHz
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; I_{e} = 0 A; I_{e} = 1 MHz; I_{CB} = 25 °C	-	58	-	pF

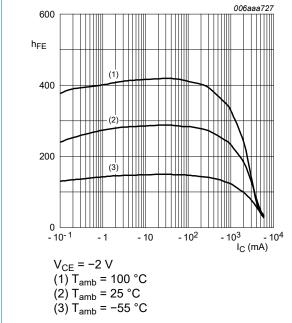


Fig. 6. DC current gain as a function of collector current; typical values

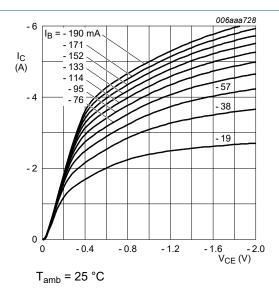


Fig. 7. Collector current as a function of collectoremitter voltage; typical values

- 1.2

V_{BEsat} (V)

- 0.8

-0.4

- 10⁻¹

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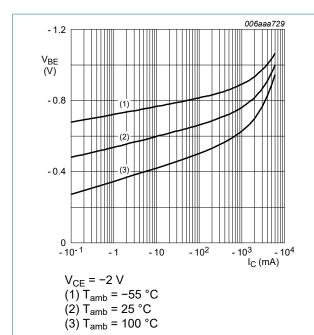


Fig. 9. Base-emitter saturation voltage as a function of collector current; typical values

- 10

- 10²

- 10³

- 10⁴



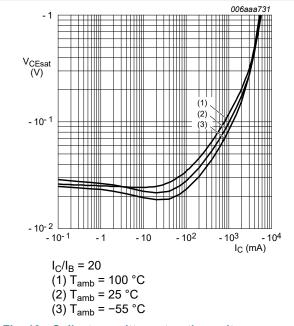


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

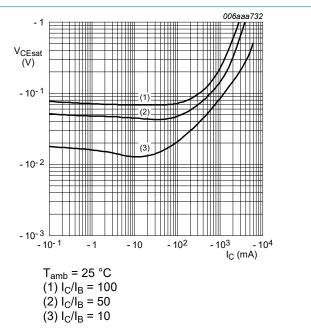


Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values

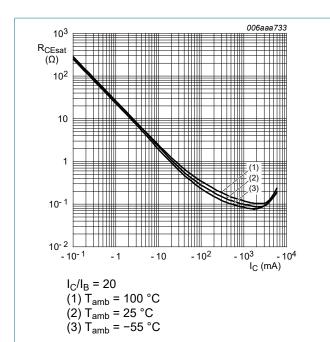


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

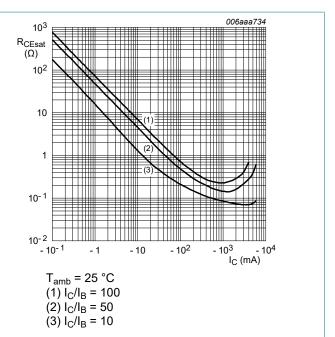


Fig. 13. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

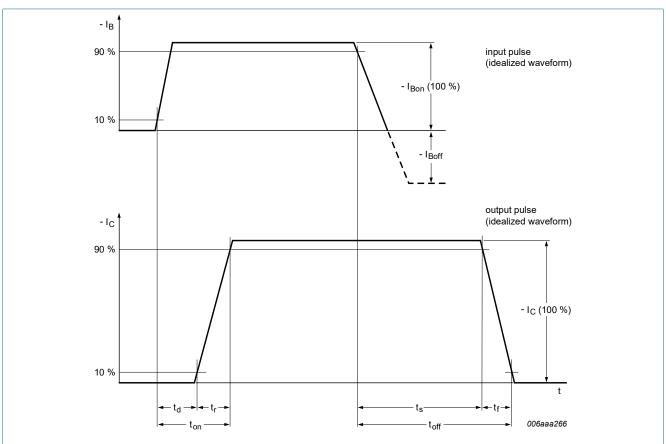


Fig. 14. Transistor switching time definition

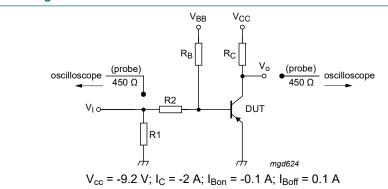
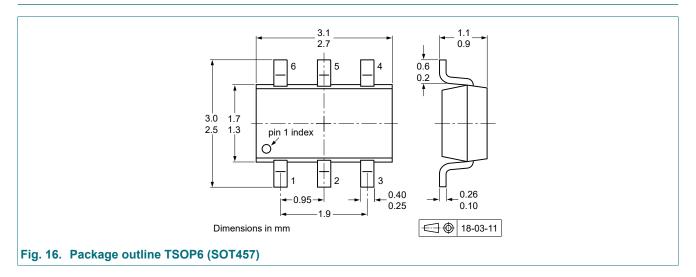


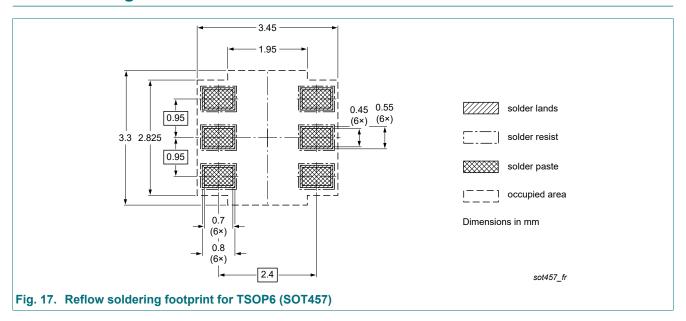
Fig. 15. Test circuit for switching times

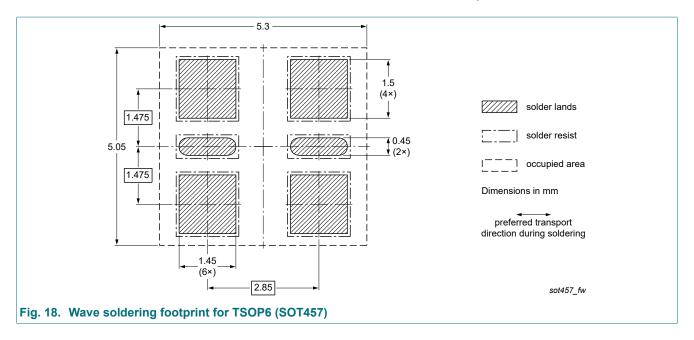
60 V, 3 A PNP low VCEsat transistor

12. Package outline



13. Soldering





60 V, 3 A PNP low VCEsat transistor

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS303PD v.3	20230915	Product data sheet	-	PBSS303PD_2	
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Section "Packing information" removed. 				
PBSS303PD_2	20091120	Product data sheet	-	PBSS303PD_1	
PBSS303PD_1	20060531	Product data sheet	-	-	

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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